

Replace the paragraph beginning at page 2, line 10, with:

The polysilicon film is etched through the mask member in an atmosphere prepared by converting a gas mixture containing Cl_2 and O_2 or HBr , Cl_2 and O_2 , for example, into a plasma, patterning the gate electrode. In this patterning, a reaction product adheres to the side wall surfaces of the gate electrode and the surface of the mask member. After formation of the gate electrode, the reaction product adhering to the gate electrode is removed by wet cleaning.

Replace the paragraph beginning at page 2, line 17, with:

It is known that the reaction product is mainly composed of a silicon oxide such as SiO_xCl_y or SiO_xBr_y when the polysilicon film is etched by converting the gas mixture containing Cl_2 and O_2 or HBr , Cl_2 , and O_2 to a plasma.

Replace the paragraph beginning at page 3, line 26, with:

In this case, the etched portion may not be fully filled but produce a void when the gate electrode 103 is covered with an interlayer isolation film, and reduce the reliability of the semiconductor device.

IN THE CLAIMS

Replace the indicated claims with:

1. (Amended) A method of fabricating a semiconductor device comprising a wafer treatment of a first part of the wafer having a first etching property and a second part of the wafer having a second etching property different from the first etching property, in a chamber with a gas for etching, including:
introducing the gas for etching into the chamber, and